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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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HSB2838

Silicon Epitaxial Planar Diode for High Speed Switching

RENESAS

ADE-208-486A (Z)

Rev.1 Mar. 2002

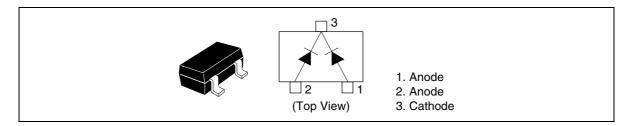
Features

- Fast recovery time.
- CMPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Туре No.	Laser Mark	Package Code
HSB2838	A6	СМРАК

Pin Arrangement



HSB2838

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit
Peak reverse voltage	V _{RM}	85	V
Reverse voltage	V _R	80	V
Average rectified current	l _o * ¹	100	mA
Peak forward current	ا _{= ۲M} ا	300	mA
Non-Repetitive peak forward surge current	I _{FSM} * ²	4	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Notes: 1. Two device total.

2. Value at duration of 1 μ sec, two device total.

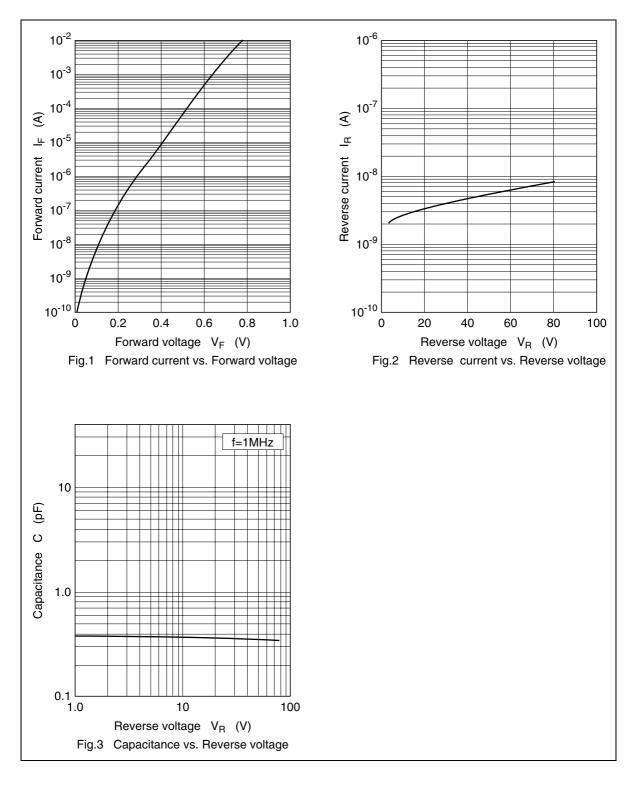
Electrical Characteristics *

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V _{F1}			1.0	V	I _F = 10 mA
	V _{F2}			1.0		$I_{\rm F} = 50 \text{ mA}$
	V _{F3}	_	_	1.2		I _F = 100 mA
Reverse current	I _R			0.1	μA	V _R = 80 V
Capacitance	С	_	_	2.0	pF	$V_{_{\mathrm{R}}} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$
Reverse recovery time	t _{rr}			3.0	ns	$I_{_{\rm F}}$ = 10 mA, $V_{_{\rm R}}$ = 6 V, $R_{_{\rm L}}$ = 50 Ω

Note: Per one device.

Main Characteristic



HSB2838

Package Dimensions

